DRV5013-Q1 汽车类数字锁存霍尔效应传感器

1 特性

- 符合面向汽车应用的 AEC-Q100 标准：
  - 器件 HBM ESD 分类等级 2
  - 器件 CDM ESD 分类等级 C4B
  - 1 级：T_A = –40°C 至 125°C（Q，请参阅*器件命名规则*）
  - 0 级：T_A = –40°C 至 150°C（E，请参阅*器件命名规则*）
- 数字双极锁存霍尔传感器
- 出色的温度稳定性
  - 在温度范围内 B_{OP} ±10%
- 多种灵敏度选项 (B_{OP}/B_{RP})
  - 1.3/–1.3mT（FA，请参阅 *器件命名规则*）
  - 2.7/–2.7mT（AD，请参阅 *器件命名规则*）
  - 6/–6mT（AG，请参阅 *器件命名规则*）
  - 12/–12mT（BC，请参阅 *器件命名规则*）
- 支持宽电压范围
  - 2.7V 至 38V
  - 无需外部稳压器
- 开漏输出（30mA 灌电流）
- 35µs 短暂上电时间
- 小型封装尺寸
  - 表面贴装 3 引脚小外形尺寸晶体管 (SOT)-23 (DBZ)
    - 2.92mm × 2.37mm
  - 插入式 3 引脚 TO-92 (LPG)
    - 4.00mm × 3.15mm
- 保护 特性
  - 反向电源保护（高达 -22V）
  - 支持高达 40V 抛负载
  - 输出短路保护
  - 输出电流限制
  - 电池输出短路保护

2 应用

- 电动工具
- 流量计
- 阀门和螺线管状态
- 无刷直流电机
- 接近感测
- 转速计

3 说明

DRV5013-Q1 器件是一款斩波稳定霍尔效应传感器，能够在整个温度范围内提供具有出色灵敏度稳定性和集成保护特性的磁场感测 特性。

磁场由数字双极锁存输出表示。该集成电路 (IC) 配有一个灌电流能力达 30mA 的漏极开路输出级。反向极性保护高达 -22V 的宽工作电压范围（2.7 至 38V）使得此器件广泛适用于各种汽车 应用。

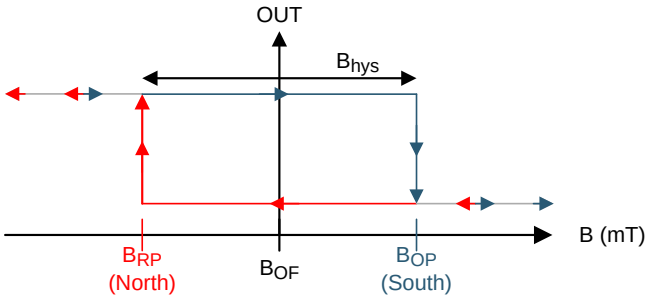
提供针对反向电源情况、抛负载和输出短路或者过流的内部保护功能。

器件信息(1)

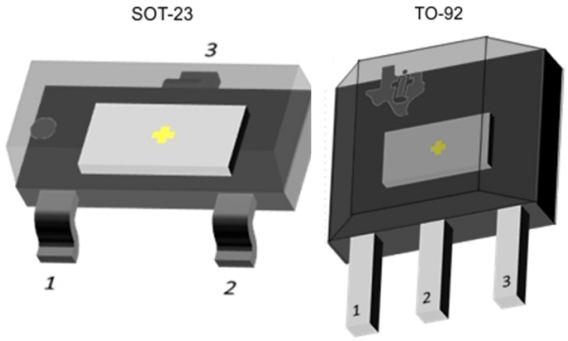
器件型号	封装	封装尺寸（标称值）
DRV5013-Q1	SOT-23 (3)	2.92mm × 1.30mm
	TO-92 (3)	4.00mm × 3.15mm

(1) 如需了解所有可用封装，请参阅数据表末尾的封装选项附录。

输出状态



器件封装



本文档旨在为方便起见，提供有关 TI 产品中文版本的信息，以确认产品的概要。 有关适用的官方英文版本的最新信息，请访问 www.ti.com，其内容始终优先。 TI 不保证翻译的准确性和有效性。 在实际设计之前，请务必参考最新版本的英文版本。

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4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision G (October 2017) to Revision H — **Page**

- Changed *Power Supply Recommendations* section ... 19

Changes from Revision F (September 2016) to Revision G — **Page**

- 已更改 将特定于汽车的 特性 项目符号位置更改到了 特性 部分顶部 ... 1
- 已添加 向特定于汽车的*特性*特性项目符号中添加了器件 HBM 和 CDM 分类子项目符号 ... 1
- Added last sentence to *Device Functional Modes* section ... 16

Changes from Revision E (August 2016) to Revision F — **Page**

- Made changes to the Power-on time in the *Electrical Characteristics* table ... 6

Changes from Revision D (June 2016) to Revision E — **Page**

- Revised preliminary limits for FA version in the *Magnetic Characteristics* table ... 7
- Added the *Layout* section ... 20

Changes from Revision C (May 2016) to Revision D — **Page**

- Revised preliminary limits for the FA version ... 7

Changes from Revision B (February 2016) to Revision C — **Page**

- Revised preliminary limits for the FA version ... 7

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Changes from Revision A (December 2015) to Revision B **Page**

- 已添加 FA 器件选项 1
- Added the typical bandwidth value to the *Magnetic Characteristics* table 7

Changes from Original (December 2014) to Revision A **Page**

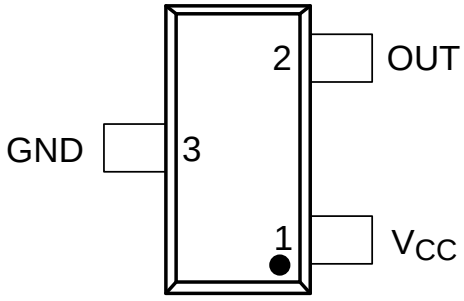
- 已更正 SOT-23 封装体尺寸并将 SIP 封装名称更正为 TO-92 1
- Added B_{MAX} to *Absolute Maximum Ratings* 5
- Removed table notes regarding testing for the operating junction temperature in *Absolute Maximum Ratings* 5
- 已更新封装卷带选项 M 和空白 21
- 已添加 *社区资源* 22

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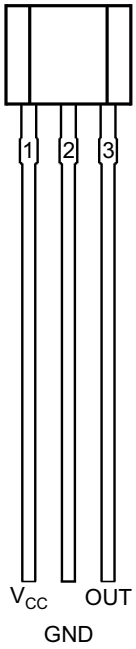
5 Pin Configuration and Functions

For additional configuration information, see *器件标记* and *机械、封装和可订购信息*.

DBZ Package
3-Pin SOT-23
Top View



LPG Package
3-Pin TO-92
Top View



Pin Functions

PIN			TYPE	DESCRIPTION
NAME	DBZ	LPG		
GND	3	2	GND	Ground pin
OUT	2	3	Output	Hall sensor open-drain output. The open drain requires a resistor pullup.
V_{CC}	1	1	PWR	2.7 to 38 V power supply. Bypass this pin to the GND pin with a 0.01-µF (minimum) ceramic capacitor rated for V_{CC}.

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6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
Power supply voltage	V_{CC}	–22 (2)	40	V
	Voltage ramp rate (V_{CC}), V_{CC} < 5 V	Unlimited		V/µs
	Voltage ramp rate (V_{CC}), V_{CC} > 5 V	0	2	
Output pin voltage		–0.5	40	V
Output pin reverse current during reverse supply condition		0	100	mA
Magnetic flux density, B_{MAX}		Unlimited		
Operating junction temperature, T_J	Q, see 图 24	–40	150	°C
	E, see 图 24	–40	175	
Storage temperature, T_{stg}		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) Ensured by design. Only tested to –20 V.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 (1)	±2500	V
		Charged-device model (CDM), per AEC Q100-011	±500	

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Power supply voltage		2.7	38	V
V_O	Output pin voltage (OUT)		0	38	V
I_{SINK}	Output pin current sink (OUT) (1)		0	30	mA
T_A	Operating ambient temperature	Q, see 图 24	–40	125	°C
		E, see 图 24	–40	150	

(1) Power dissipation and thermal limits must be observed

6.4 Thermal Information

THERMAL METRIC (1)		DRV5013-Q1		UNIT
		DBZ (SOT-23)	LPG (TO-92)	
		3 PINS	3 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	333.2	180	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	99.9	98.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	66.9	154.9	°C/W
ψ_{JT}	Junction-to-top characterization parameter	4.9	40	°C/W
ψ_{JB}	Junction-to-board characterization parameter	65.2	154.9	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

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6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER SUPPLIES (V_{CC})						
V_{CC}	V_{CC} operating voltage		2.7		38	V
I_{CC}	Operating supply current	V_{CC} = 2.7 to 38 V, T_A = 25°C		2.7		mA
		V_{CC} = 2.7 to 38 V, T_A = $T_{A, MAX}$ (1)		3	3.5	
t_{on}	Power-on time	AD, AG, BC versions		35	50	µs
		FA version		35	70	
OPEN DRAIN OUTPUT (OUT)						
$r_{DS(on)}$	FET on-resistance	V_{CC} = 3.3 V, I_O = 10 mA, T_A = 25°C		22		Ω
		V_{CC} = 3.3 V, I_O = 10 mA, T_A = 125°C		36	50	
$I_{lkg(off)}$	Off-state leakage current	Output Hi-Z			1	µA
PROTECTION CIRCUITS						
V_{CCR}	Reverse supply voltage		–22			V
I_{OCP}	Overcurrent protection level	OUT shorted V_{CC}	15	30	45	mA

(1) $T_{A, MAX}$ is 125°C for Q Grade 1 devices and 150°C for E Grade 0 devices (see 图 24)

6.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OPEN DRAIN OUTPUT (OUT)						
t_d	Output delay time	B = B_{RP} – 10 mT to B_{OP} + 10 mT in 1 µs		13	25	µs
t_r	Output rise time (10% to 90%)	R1 = 1 kΩ, C_O = 50 pF, V_{CC} = 3.3 V		200		ns
t_f	Output fall time (90% to 10%)	R1 = 1 kΩ, C_O = 50 pF, V_{CC} = 3.3 V		31		ns

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6.7 Magnetic Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT(1)
f_{BW}	Bandwidth(2)		20	30		kHz
DRV5013FA: 1.3 / –1.3 mT						
B_{OP}	Operate point; see Figure 12		–0.6	1.3	3.4	mT
B_{RP}	Release point; see Figure 12		–3.4	–1.3	0.6	mT
B_{hys}	Hysteresis; $B_{hys} = (B_{OP} – B_{RP})$		1.2	2.6		mT
B_O	Magnetic offset; $B_O = (B_{OP} + B_{RP}) / 2$		–1.5	0	1.5	mT
DRV5013AD: 2.7 / –2.7 mT						
B_{OP}	Operate point; see Figure 12		1	2.7	5	mT
B_{RP}	Release point; see Figure 12		–5	–2.7	–1	mT
B_{hys}	Hysteresis; $B_{hys} = (B_{OP} – B_{RP})$			5.4		mT
B_O	Magnetic offset; $B_O = (B_{OP} + B_{RP}) / 2$		–1.5	0	1.5	mT
DRV5013AG: 6 / –6 mT						
B_{OP}	Operate point; see Figure 12		3	6	9	mT
B_{RP}	Release point; see Figure 12		–9	–6	–3	mT
B_{hys}	Hysteresis; $B_{hys} = (B_{OP} – B_{RP})$			12		mT
B_O	Magnetic offset; $B_O = (B_{OP} + B_{RP}) / 2$		–1.5	0	1.5	mT
DRV5013BC: 12 / –12 mT						
B_{OP}	Operate point; see Figure 12		6	12	18	mT
B_{RP}	Release point; see Figure 12		–18	–12	–6	mT
B_{hys}	Hysteresis; $B_{hys} = (B_{OP} – B_{RP})$			24		mT
B_O	Magnetic offset; $B_O = (B_{OP} + B_{RP}) / 2$		–1.5	0	1.5	mT

(1) 1 mT = 10 Gauss
(2) Bandwidth describes the fastest changing magnetic field that can be detected and translated to the output.

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6.8 Typical Characteristics

T_A > 125°C data is valid for Grade 0 devices only (E, see 图 24)

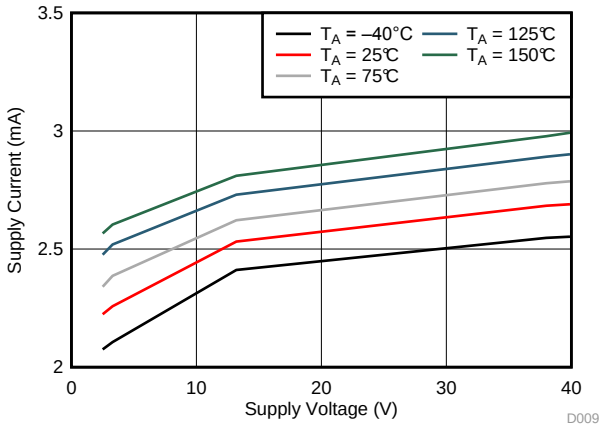


Figure 1. I_{CC} vs V_{CC}

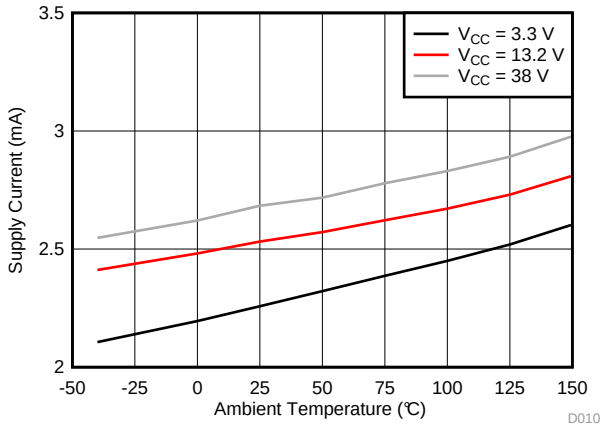


Figure 2. I_{CC} vs Temperature

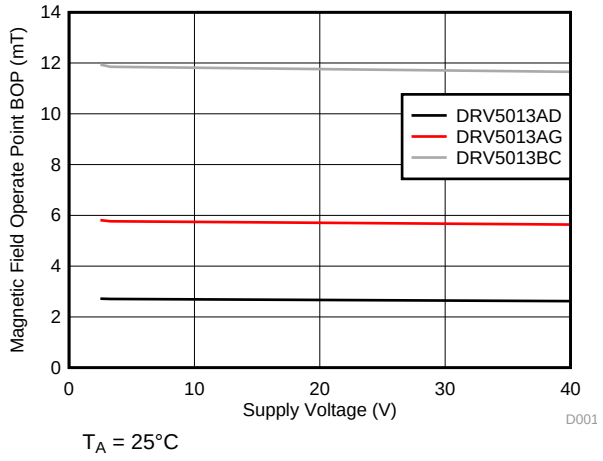


Figure 3. B_{OP} vs V_{CC}

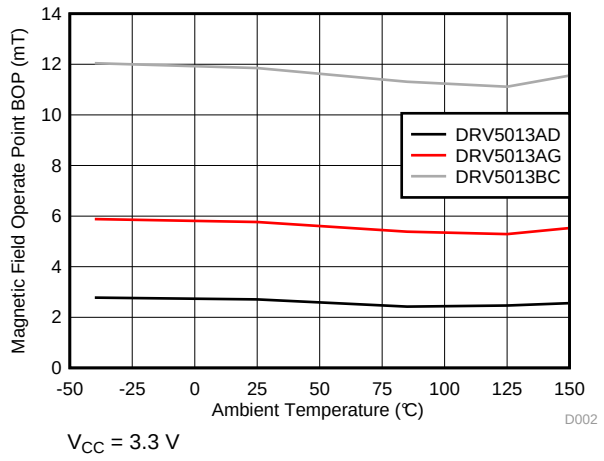


Figure 4. B_{OP} vs Temperature

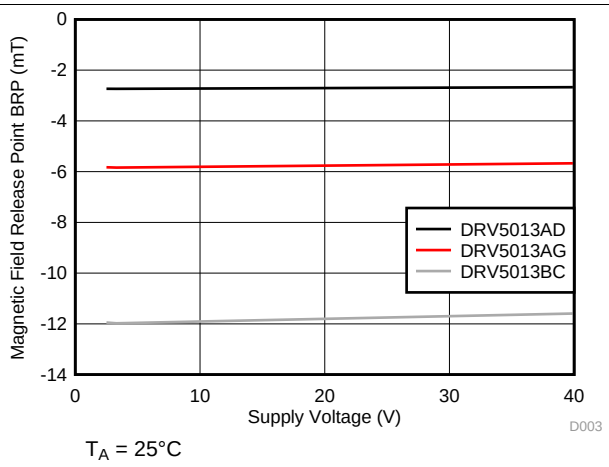


Figure 5. B_{RP} vs V_{CC}

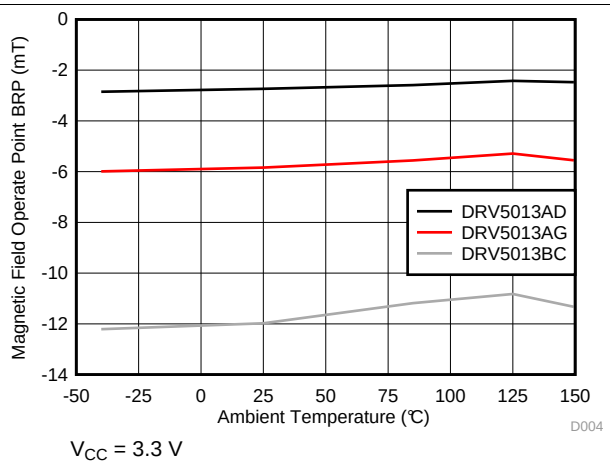


Figure 6. B_{RP} vs Temperature

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Typical Characteristics (continued)

T_A > 125°C data is valid for Grade 0 devices only (E, see 图 24)

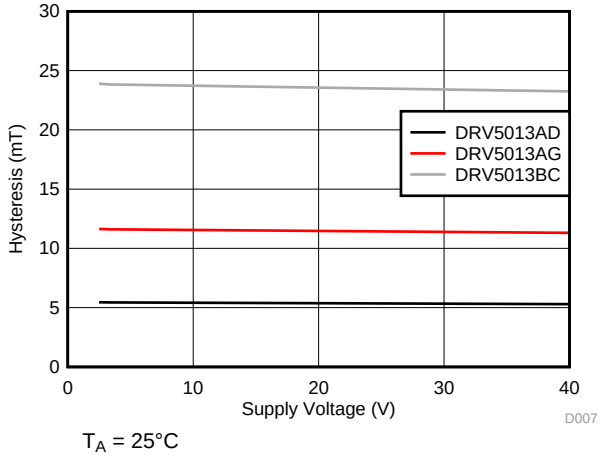


Figure 7. Hysteresis vs V_{CC}

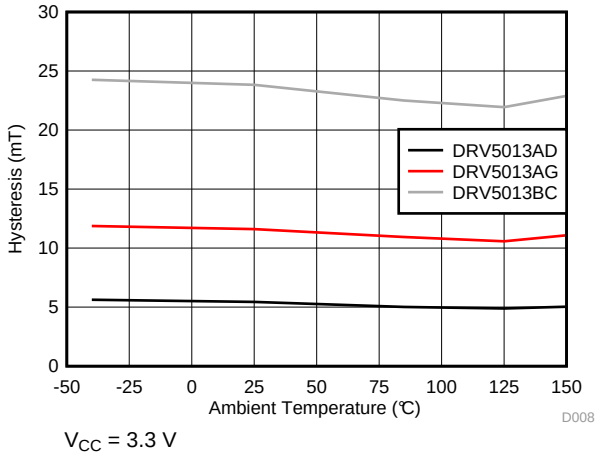


Figure 8. Hysteresis vs Temperature

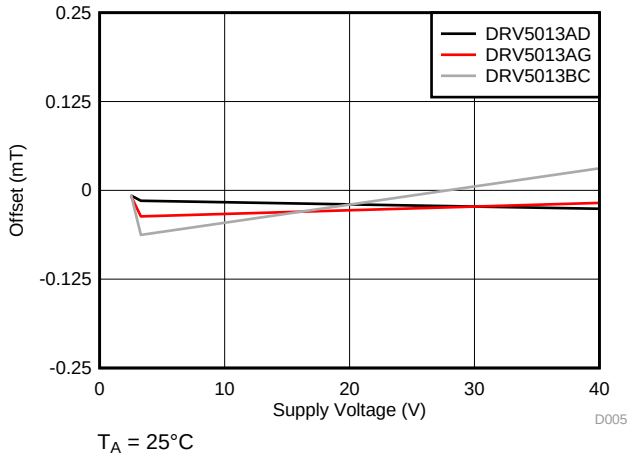


Figure 9. Offset vs V_{CC}

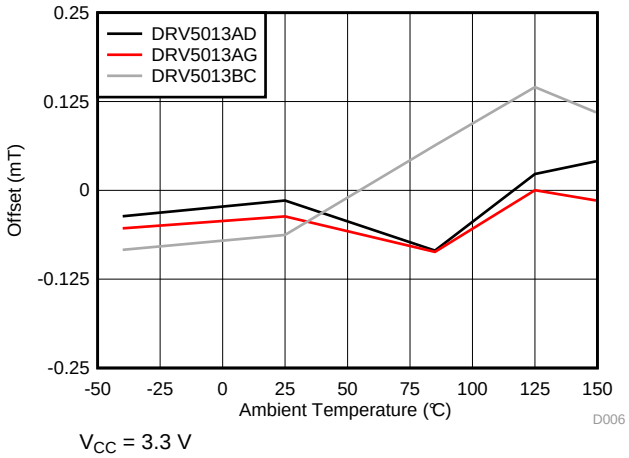


Figure 10. Offset vs Temperature

7 Detailed Description

7.1 Overview

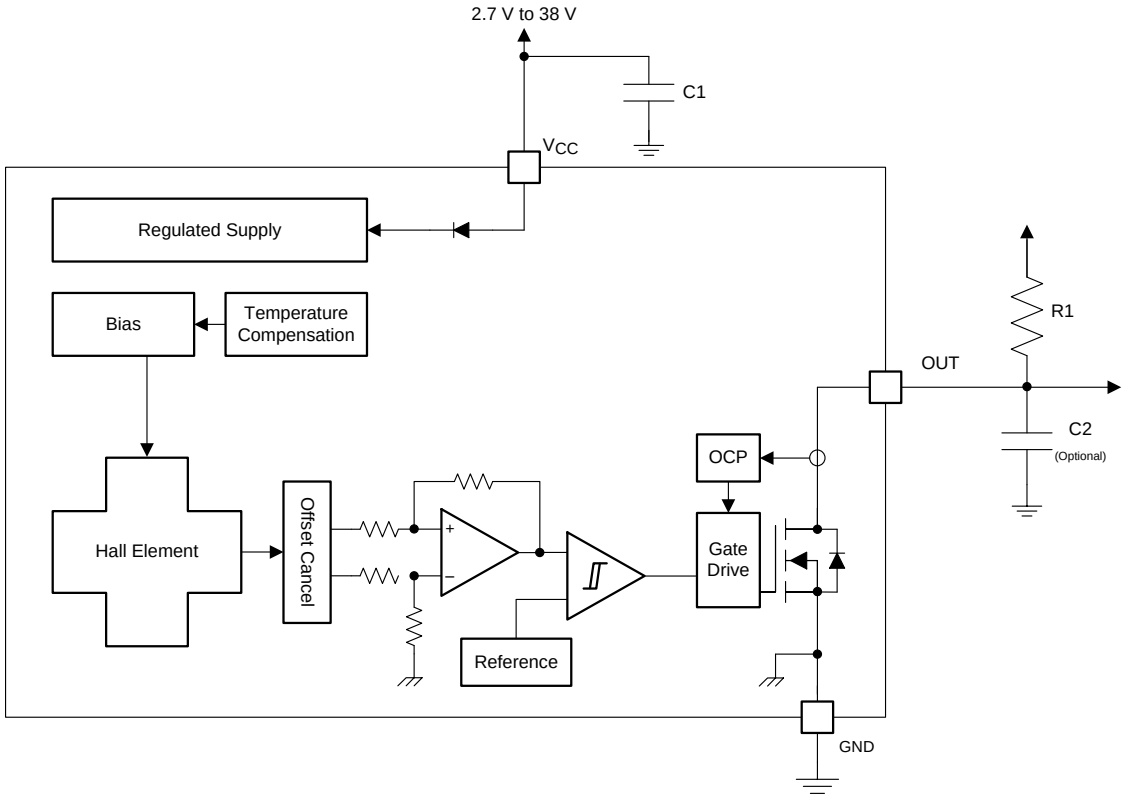
The DRV5013-Q1 device is a chopper-stabilized Hall sensor with a digital latched output for magnetic sensing applications. The DRV5013-Q1 device can be powered with a supply voltage between 2.7 and 38 V, and continuously survives continuous –22-V reverse-battery conditions. The DRV5013-Q1 device does not operate when –22 to 2.4 V is applied to the V_{CC} pin (with respect to the GND pin). In addition, the device can withstand voltages up to 40 V for transient durations.

The field polarity is defined as follows: a south pole near the marked side of the package is a positive magnetic field. A north pole near the marked side of the package is a negative magnetic field.

The output state is dependent on the magnetic field perpendicular to the package. A south pole near the marked side of the package causes the output to pull low (operate point, B_{OP}), and a north pole near the marked side of the package causes the output to release (release point, B_{RP}). Hysteresis is included in between the operate point and the release point therefore magnetic-field noise does not accidentally trip the output.

An external pullup resistor is required on the OUT pin. The OUT pin can be pulled up to V_{CC}, or to a different voltage supply. This allows for easier interfacing with controller circuits.

7.2 Functional Block Diagram



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7.3 Feature Description

7.3.1 Field Direction Definition

A positive magnetic field is defined as a south pole near the marked side of the package as shown in Figure 11.

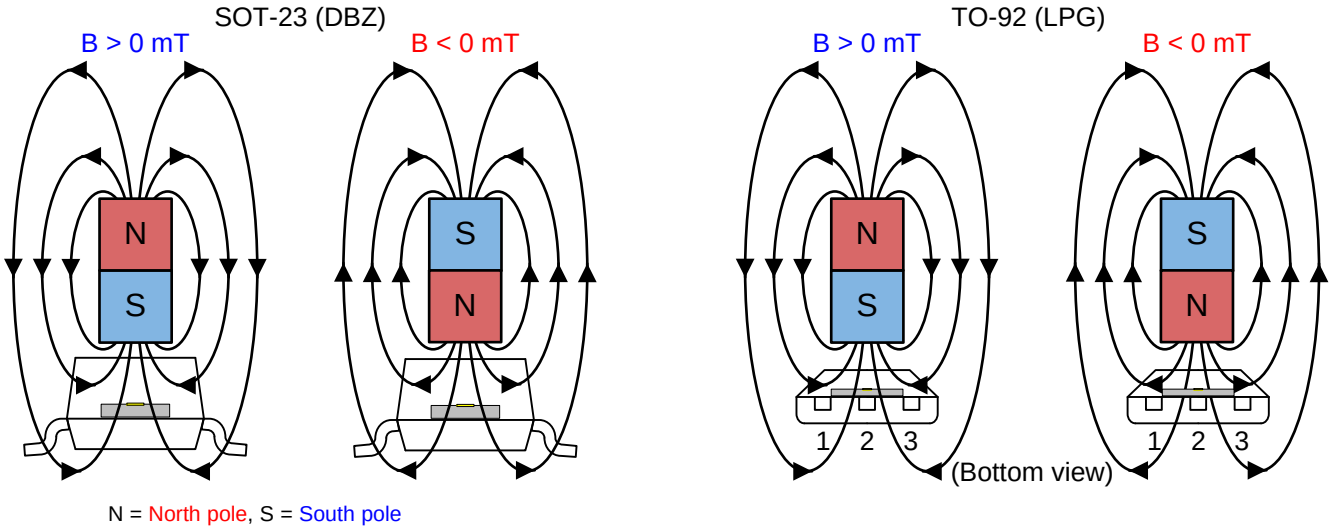


Figure 11. Field Direction Definition

7.3.2 Device Output

If the device is powered on with a magnetic field strength between B_{RP} and B_{OP}, then the device output is indeterminate and can either be Hi-Z or Low. If the field strength is greater than B_{OP}, then the output is pulled low. If the field strength is less than B_{RP}, then the output is released.

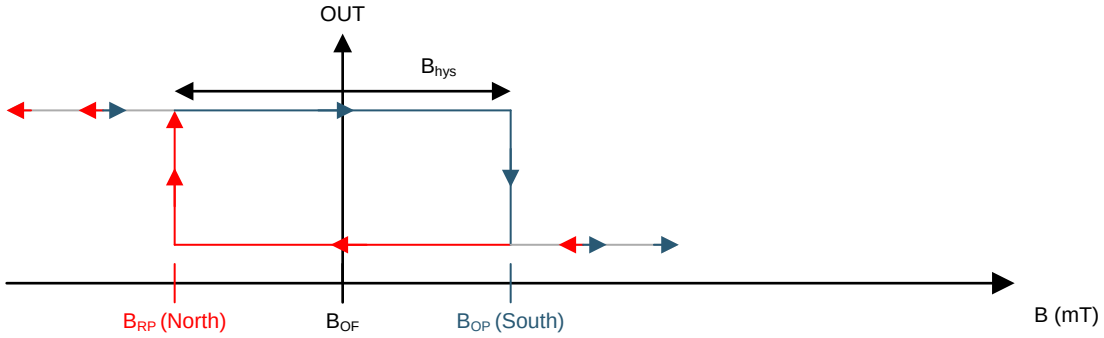


Figure 12. DRV5013-Q1—B_{OP} > 0

Feature Description (continued)

7.3.3 Power-On Time

After applying V_{CC} to the DRV5013-Q1 device, t_{on} must elapse before the OUT pin is valid. During the power-up sequence, the output is Hi-Z. A pulse as shown in Figure 13 and Figure 14 occurs at the end of t_{on}. This pulse can allow the host processor to determine when the DRV5013-Q1 output is valid after startup. In Case 1 (Figure 13) and Case 2 (Figure 14), the output is defined assuming a constant magnetic field B > B_{OP} and B < B_{RP}.

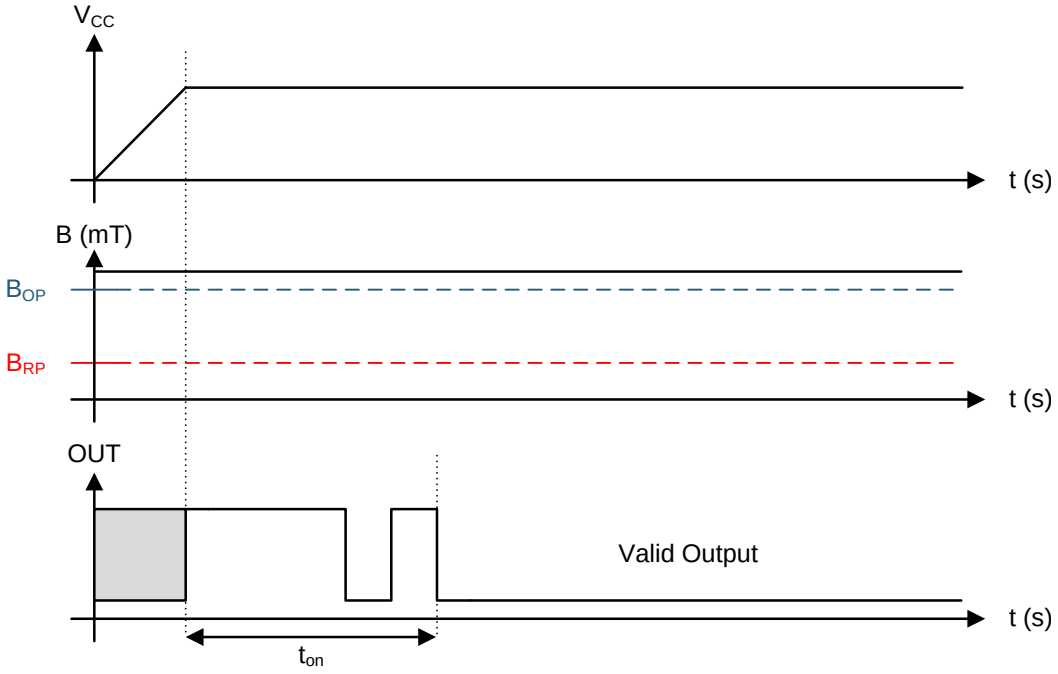


Figure 13. Case 1: Power On When B > B_{OP}

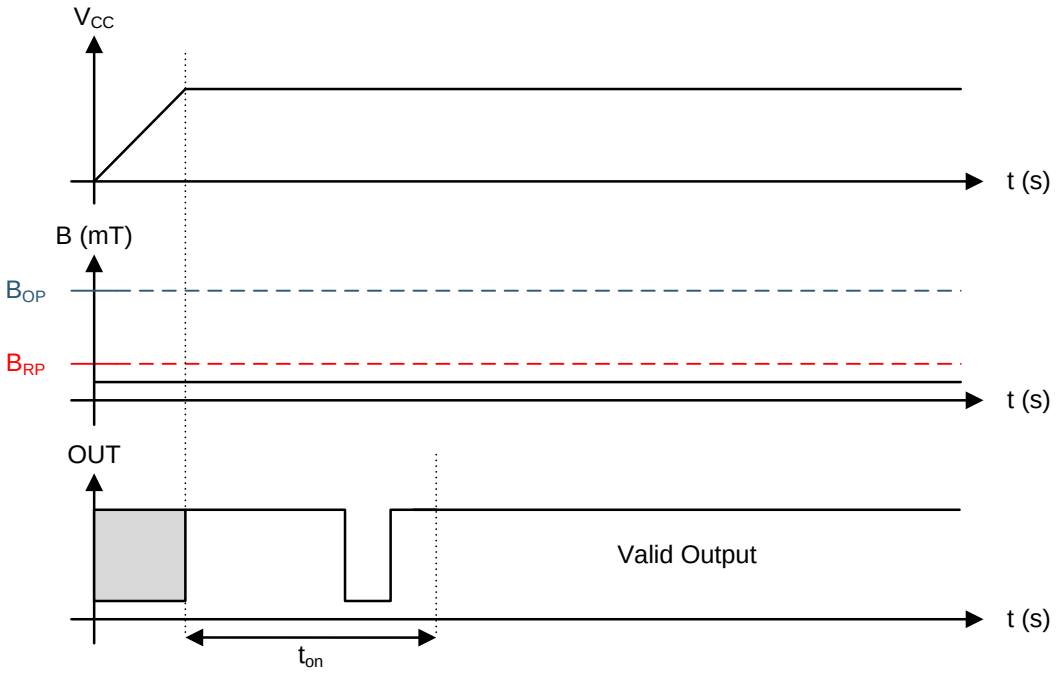


Figure 14. Case 2: Power On When B < B_{RP}

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Feature Description (continued)

If the device is powered on with the magnetic field strength $B_{RP} < B < B_{OP}$, then the device output is indeterminate and can either be Hi-Z or pulled low. During the power-up sequence, the output is held Hi-Z until t_{on} has elapsed. At the end of t_{on}, a pulse is given on the OUT pin to indicate that t_{on} has elapsed. After t_{on}, if the magnetic field changes such that $B_{OP} < B$, the output is released. Case 3 (Figure 15) and Case 4 (Figure 16) show examples of this behavior.

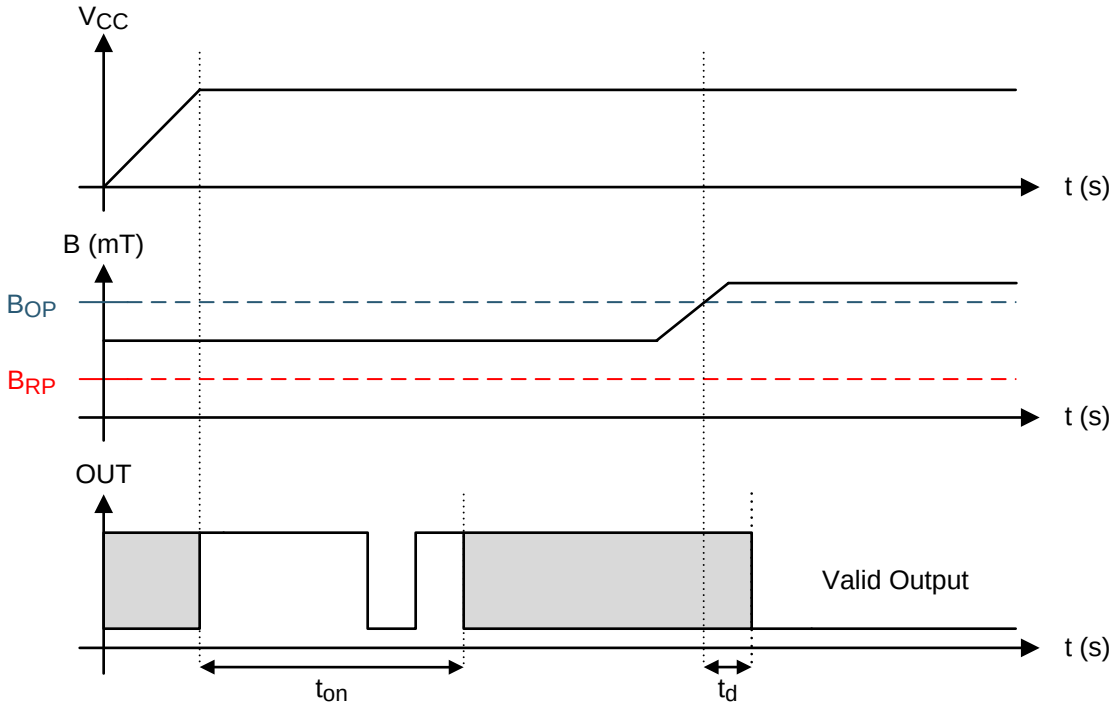


Figure 15. Case 3: Power On When $B_{RP} < B < B_{OP}$, Followed by $B > B_{OP}$

Feature Description (continued)

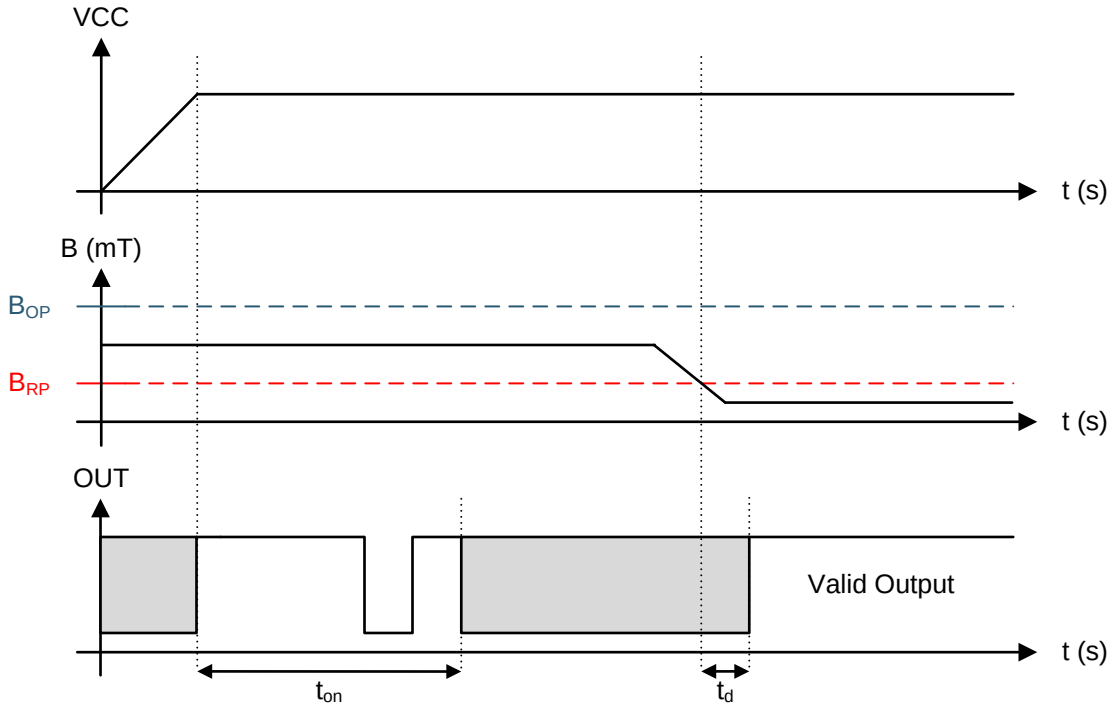


Figure 16. Case 4: Power On When B_{RP} < B < B_{OP}, Followed by B < B_{RP}

7.3.4 Output Stage

The DRV5013-Q1 output stage uses an open-drain NMOS, and it is rated to sink up to 30 mA of current. For proper operation, calculate the value of the pullup resistor R1 using Equation 1.

$$\frac{V_{ref}\,max}{30\ mA} \le R1 \le \frac{V_{ref}\,min}{100\ \mu A} \quad (1)$$

The size of R1 is a tradeoff between the OUT rise time and the current when OUT is pulled low. A lower current is generally better, however faster transitions and bandwidth require a smaller resistor for faster switching.

In addition, ensure that the value of R1 > 500 Ω to ensure the output driver can pull the OUT pin close to GND.

NOTE

V_{ref} is not restricted to V_{CC}. The allowable voltage range of this pin is specified in the *Absolute Maximum Ratings*.

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Feature Description (continued)

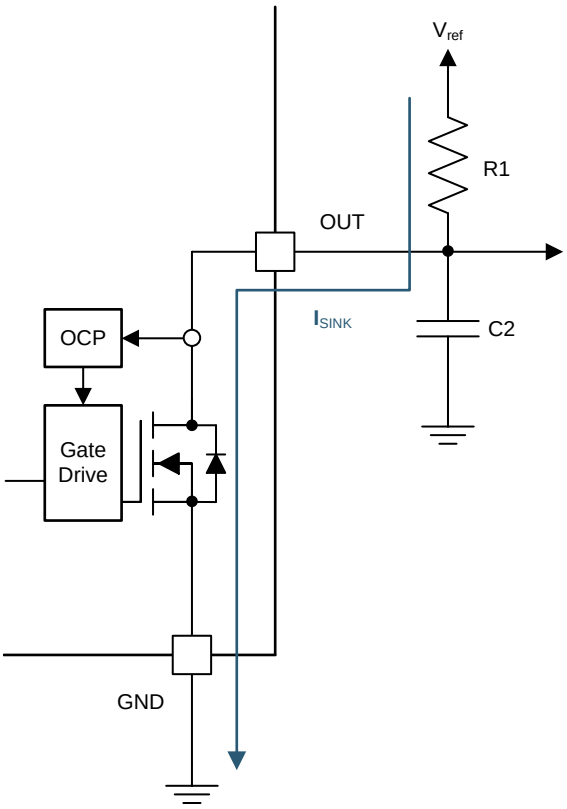


Figure 17.

Select a value for C2 based on the system bandwidth specifications as shown in Equation 2.

$$2 \times f_{BW}\ (\text{Hz}) < \frac{1}{2\pi \times R1 \times C2} \tag{2}$$

Most applications do not require this C2 filtering capacitor.

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Feature Description (continued)

7.3.5 Protection Circuits

The DRV5013-Q1 device is fully protected against overcurrent and reverse-supply conditions.

7.3.6 Overcurrent Protection (OCP)

An analog current-limit circuit limits the current through the FET. The driver current is clamped to I_{OCP}. During this clamping, the $r_{DS(on)}$ of the output FET is increased from the nominal value.

7.3.7 Load Dump Protection

The DRV5013-Q1 device operates at DC V_{CC} conditions up to 38 V nominally, and can additionally withstand V_{CC} = 40 V. No current-limiting series resistor is required for this protection.

7.3.8 Reverse Supply Protection

The DRV5013-Q1 device is protected in the event that the V_{CC} pin and the GND pin are reversed (up to –22 V).

NOTE

In a reverse supply condition, the OUT pin reverse-current must not exceed the ratings specified in the *Absolute Maximum Ratings*.

Table 1.

FAULT	CONDITION	DEVICE	DESCRIPTION	RECOVERY
FET overload (OCP)	$I_{SINK} \geq I_{OCP}$	Operating	Output current is clamped to I_{OCP}	$I_O < I_{OCP}$
Load dump	38 V < V_{CC} < 40 V	Operating	Device will operate for a transient duration	$V_{CC} \leq$ 38 V
Reverse supply	–22 V < V_{CC} < 0 V	Disabled	Device will survive this condition	$V_{CC} \geq$ 2.7 V

7.4 Device Functional Modes

The DRV5013-Q1 device is active only when V_{CC} is between 2.7 and 38 V.

When a reverse supply condition exists, the device is inactive. With regard to some industry standards that require analyzing every possible output from a device, an internal clock is unlikely to couple to the output.

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8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The DRV5013-Q1 device is used in magnetic-field sensing applications.

8.2 Typical Applications

8.2.1 Standard Circuit

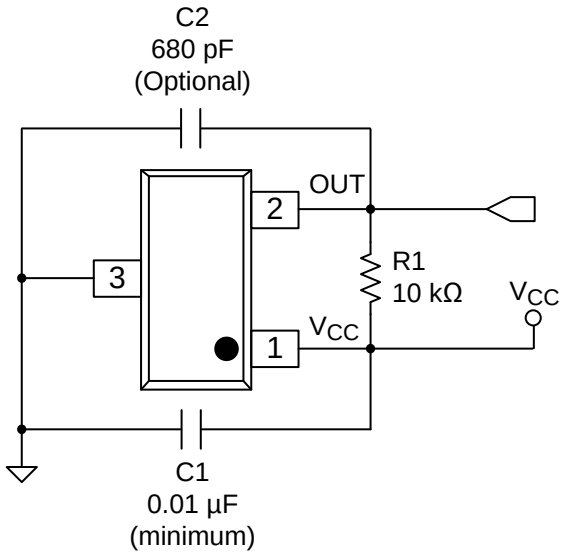


Figure 18. Typical Application Circuit

8.2.1.1 Design Requirements

For this design example, use the parameters listed in Table 2 as the input parameters.

Table 2. Design Parameters

DESIGN PARAMETER	REFERENCE	EXAMPLE VALUE
Supply voltage	V_{CC}	3.2 to 3.4 V
System bandwidth	f_{BW}	10 kHz

8.2.1.2 Detailed Design Procedure

Table 3. External Components

COMPONENT	PIN 1	PIN 2	RECOMMENDED
C1	V_{CC}	GND	A 0.01-µF (minimum) ceramic capacitor rated for V_{CC}
C2	OUT	GND	**Optional**: Place a ceramic capacitor to GND
R1	OUT	REF(1)	Requires a resistor pullup

(1) REF is not a pin on the DRV5013-Q1 device, but a REF supply-voltage pullup is required for the OUT pin; the OUT pin may be pulled up to V_{CC}.

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8.2.1.2.1 Configuration Example

In a 3.3-V system, 3.2 V ≤ V_{ref} ≤ 3.4 V. Use Equation 3 to calculate the allowable range for R1.

$$\frac{V_{ref}\,max}{30\ mA} \le R1 \le \frac{V_{ref}\,min}{100\ \mu A} \tag{3}$$

For this design example, use Equation 4 to calculate the allowable range of R1.

$$\frac{3.4\ V}{30\ mA} \le R1 \le \frac{3.2\ V}{100\ \mu A} \tag{4}$$

Therefore:

$$113\ \Omega \le R1 \le 32\ k\Omega \tag{5}$$

After finding the allowable range of R1 (Equation 5), select a value between 500 Ω and 32 kΩ for R1.

Assuming a system bandwidth of 10 kHz, use Equation 6 to calculate the value of C2.

$$2 \times f_{BW}\ (Hz) < \frac{1}{2\pi \times R1 \times C2} \tag{6}$$

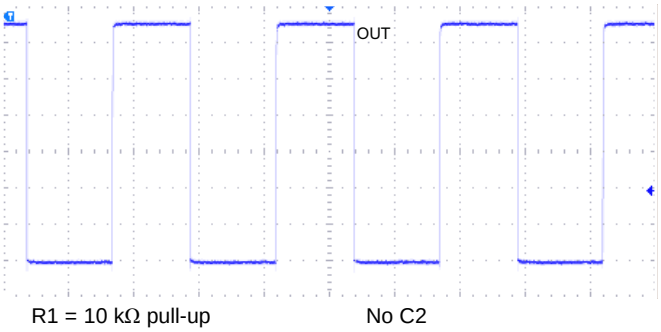
For this design example, use Equation 7 to calculate the value of C2.

$$2 \times 10\ kHz < \frac{1}{2\pi \times R1 \times C2} \tag{7}$$

An R1 value of 10 kΩ and a C2 value less than 820 pF satisfy the requirement for a 10-kHz system bandwidth.

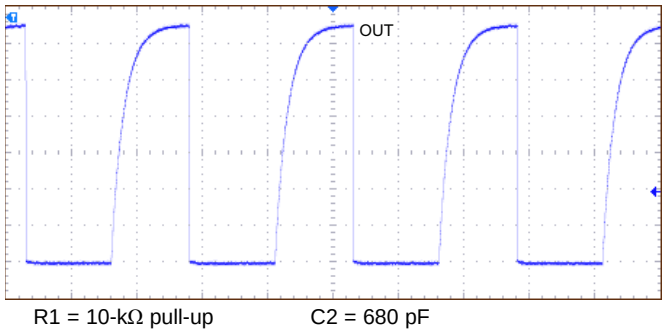
A selection of R1 = 10 kΩ and C2 = 680 pF would cause a low-pass filter with a corner frequency of 23.4 kHz.

8.2.1.3 Application Curves



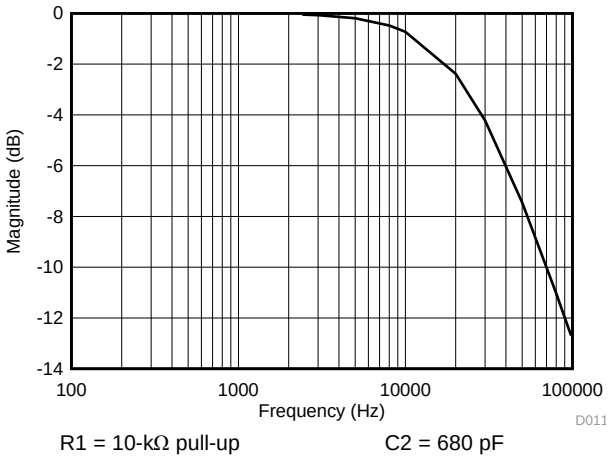
R1 = 10 kΩ pull-up No C2

Figure 19. 10-kHz Switching Magnetic Field



R1 = 10-kΩ pull-up C2 = 680 pF

Figure 20. 10-kHz Switching Magnetic Field



R1 = 10-kΩ pull-up C2 = 680 pF

Figure 21. Low-Pass Filtering

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8.2.2 Alternative Two-Wire Application

For systems that require minimal wire count, the device output can be connected to V_{CC} through a resistor, and the total supplied current can be sensed near the controller.

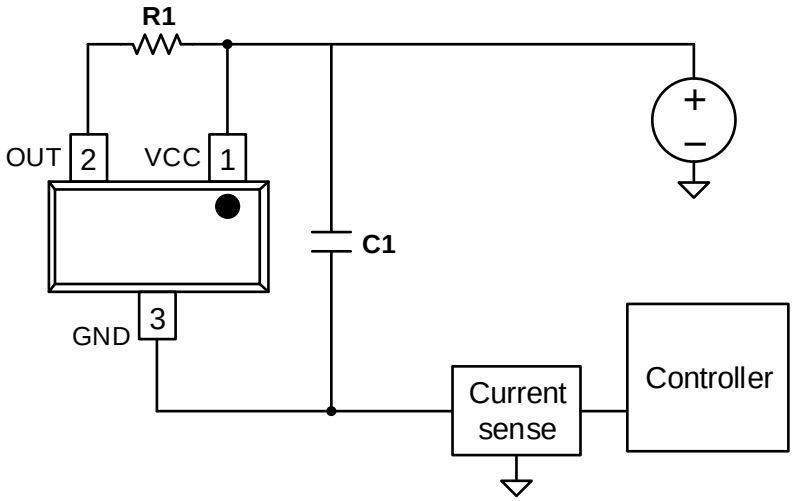


Figure 22. 2-Wire Application

Current can be sensed using a shunt resistor or other circuitry.

8.2.2.1 Design Requirements

Table 4 lists the related design parameters.

Table 4. Design Parameters

DESIGN PARAMETER	REFERENCE	EXAMPLE VALUE
Supply voltage	V_{CC}	12 V
OUT resistor	R1	1 kΩ
Bypass capacitor	C1	0.1 µF
Current when B < B_{RP}	$I_{RELEASE}$	About 3 mA
Current when B > B_{OP}	$I_{OPERATE}$	About 15 mA

8.2.2.2 Detailed Design Procedure

When the open-drain output of the device is high-impedance, current through the path equals the I_{CC} of the device (approximately 3 mA).

When the output pulls low, a parallel current path is added, equal to V_{CC} / (R1 + $r_{DS(on)}$). Using 12 V and 1 kΩ, the parallel current is approximately 12 mA, making the total current approximately 15 mA.

The local bypass capacitor C1 should be at least 0.1 µF, and a larger value if there is high inductance in the power line interconnect.

9 Power Supply Recommendations

The DRV5013-Q1 device is designed to operate from an input voltage supply (VM) range between 2.7 V and 38 V. A 0.01-µF (minimum) ceramic capacitor rated for V_{CC} must be placed as close to the DRV5013-Q1 device as possible. Larger values of the bypass capacitor may be needed to attenuate any significant high-frequency ripple and noise components generated by the power source. TI recommends limiting the supply voltage variation to less than 50 mV_{PP}.

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10 Layout

10.1 Layout Guidelines

The bypass capacitor should be placed near the DRV5013-Q1 device for efficient power delivery with minimal inductance. The external pullup resistor should be placed near the microcontroller input to provide the most stable voltage at the input; alternatively, an integrated pullup resistor within the GPIO of the microcontroller can be used.

Generally, using PCB copper planes underneath the DRV5013-Q1 device has no effect on magnetic flux, and does not interfere with device performance. This is because copper is not a ferromagnetic material. However, If nearby system components contain iron or nickel, they may redirect magnetic flux in unpredictable ways.

10.2 Layout Example

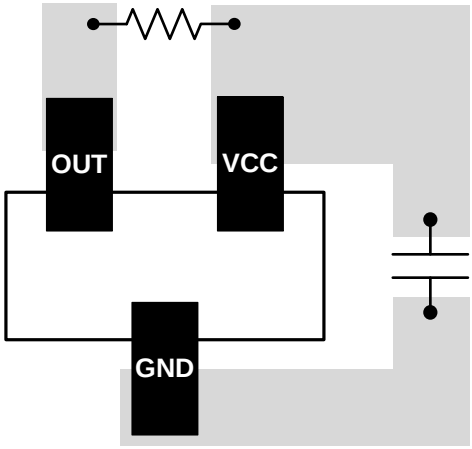


Figure 23. DRV5013-Q1 Layout Example

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11 器件和文档支持

11.1 器件支持

11.1.1 器件命名规则

图 24 显示了读取 DRV5013-Q1 器件完整器件名称的图例。

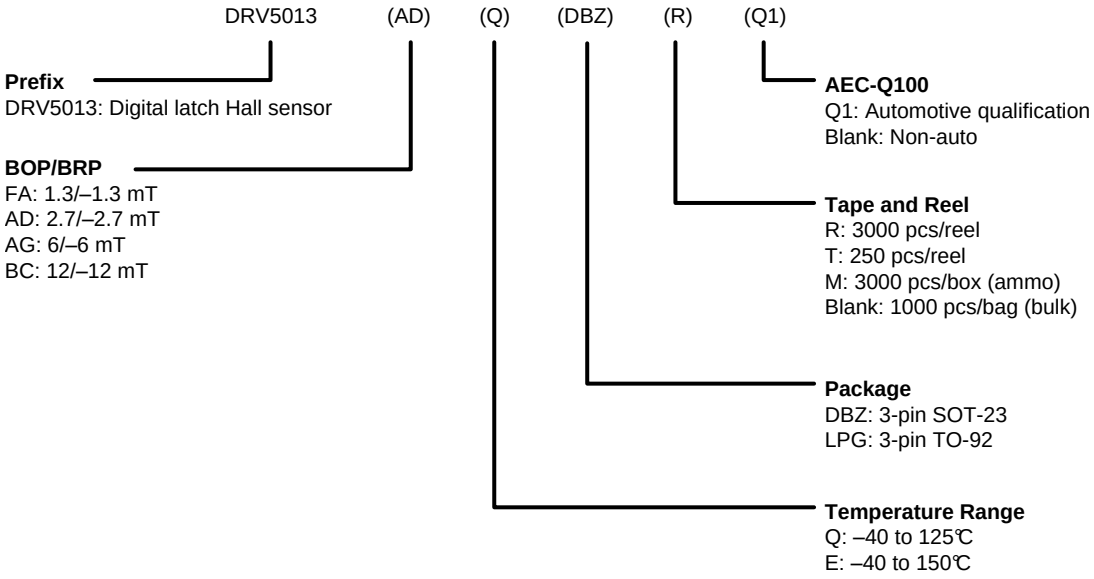


图 **24.** 器件命名规则

11.1.2 器件标记

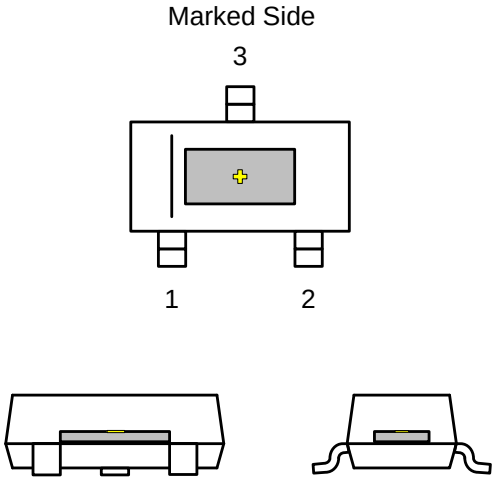


图 **25. SOT-23 (DBZ)** 封装

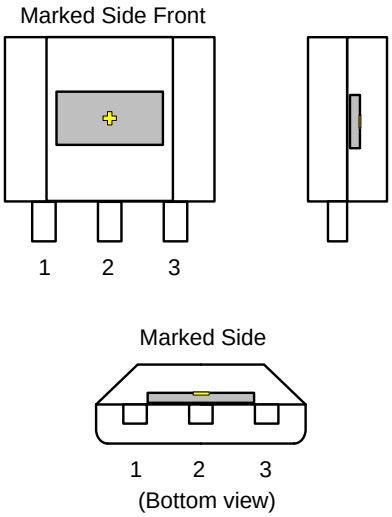


图 **26. TO-92 (LPG)** 封装

✚ 表示霍尔效应传感器（未按比例显示）。霍尔元件置于封装中央位置，容差为 ±100μm。在 DBZ 封装中，霍尔元件与封装底部的距离为 0.7mm ± 50μm；在 LPG 封装中，霍尔元件与封装底部的距离为 0.987mm ± 50μm。

11.2 接收文档更新通知

要接收文档更新通知，请转至 TI.com.cn 上您的器件的产品文件夹。请在右上角单击*通知我* 按钮进行注册，即可收到产品信息更改每周摘要（如有）。有关更改的详细信息，请查看任意已修订文档的修订历史记录。

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11.6 术语表

SLYZ022 — *TI 术语表*。

这份术语表列出并解释术语、缩写和定义。

12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DRV5013ADEDBZJQ1	ACTIVE	SOT-23	DBZ	3	10000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 150	+NJAD	Samples
DRV5013ADEDBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 150	+NJAD	Samples
DRV5013ADEDBZTQ1	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 150	+NJAD	Samples
DRV5013ADELPGMQ1	ACTIVE	TO-92	LPG	3	3000	RoHS & Green	SN	N / A for Pkg Type	-40 to 150	+NJAD	Samples
DRV5013ADELPGQ1	ACTIVE	TO-92	LPG	3	1000	RoHS & Green	SN	N / A for Pkg Type	-40 to 150	+NJAD	Samples
DRV5013ADQDBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	+NKAD	Samples
DRV5013ADQDBZTQ1	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	+NKAD	Samples
DRV5013ADQLPGMQ1	ACTIVE	TO-92	LPG	3	3000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	+NKAD	Samples
DRV5013ADQLPGQ1	ACTIVE	TO-92	LPG	3	1000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	+NKAD	Samples
DRV5013AGEDBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 150	+NJAG	Samples
DRV5013AGEDBZTQ1	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 150	+NJAG	Samples
DRV5013AGELPGMQ1	ACTIVE	TO-92	LPG	3	3000	RoHS & Green	SN	N / A for Pkg Type	-40 to 150	+NJAG	Samples
DRV5013AGELPGQ1	ACTIVE	TO-92	LPG	3	1000	RoHS & Green	SN	N / A for Pkg Type	-40 to 150	+NJAG	Samples
DRV5013AGQDBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	+NKAG	Samples
DRV5013AGQDBZTQ1	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	+NKAG	Samples
DRV5013AGQLPGMQ1	ACTIVE	TO-92	LPG	3	3000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	+NKAG	Samples
DRV5013AGQLPGQ1	ACTIVE	TO-92	LPG	3	1000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	+NKAG	Samples
DRV5013BCEDBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 150	+NJBC	Samples
DRV5013BCEDBZTQ1	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 150	+NJBC	Samples
DRV5013BCELPGMQ1	ACTIVE	TO-92	LPG	3	3000	RoHS & Green	SN	N / A for Pkg Type	-40 to 150	+NJBC	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DRV5013BCELPGQ1	ACTIVE	TO-92	LPG	3	1000	RoHS & Green	SN	N / A for Pkg Type	-40 to 150	+NJBC	Samples
DRV5013BCQDBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	+NKBC	Samples
DRV5013BCQDBZTQ1	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	+NKBC	Samples
DRV5013BCQLPGMQ1	ACTIVE	TO-92	LPG	3	3000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	+NKBC	Samples
DRV5013BCQLPGQ1	ACTIVE	TO-92	LPG	3	1000	RoHS & Green	SN	N / A for Pkg Type	-40 to 125	+NKBC	Samples
DRV5013FAEDBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 150	+NJFA	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

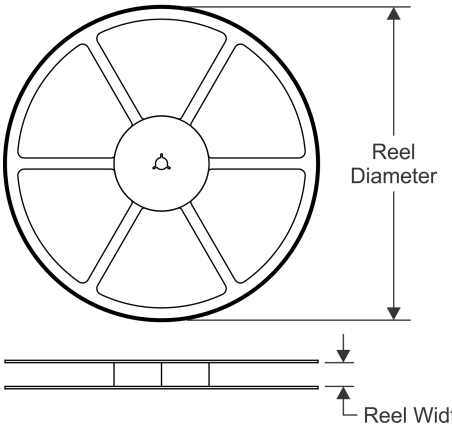
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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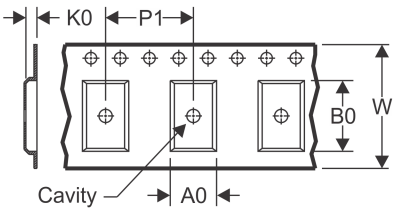
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

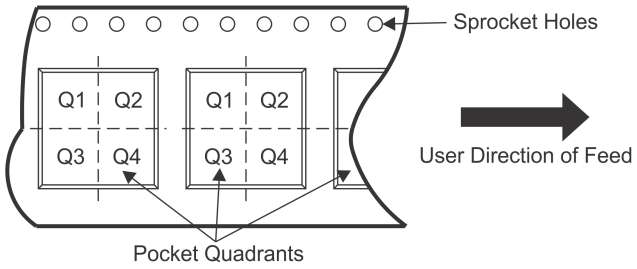


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

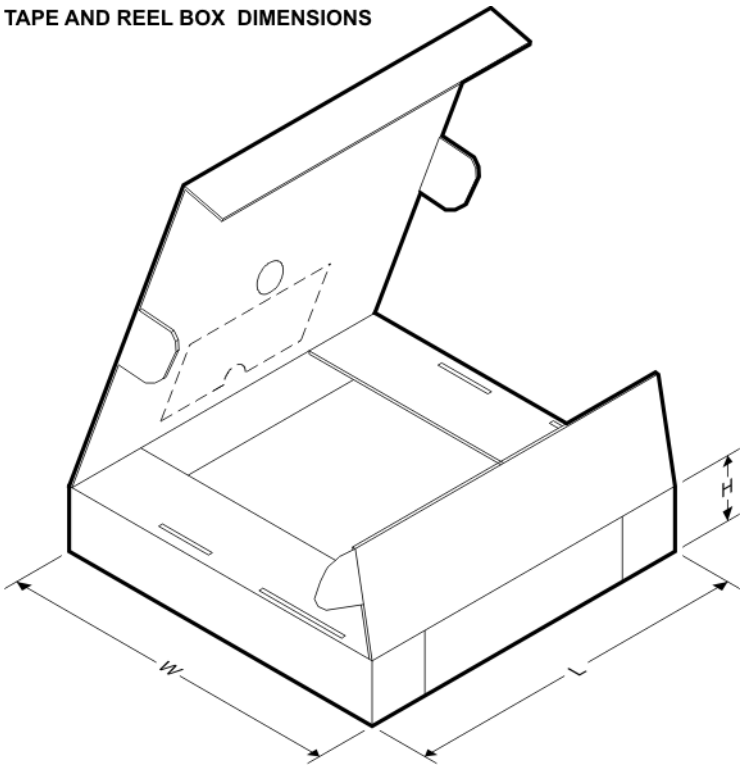
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV5013ADEDBZJQ1	SOT-23	DBZ	3	10000	330.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5013ADEDBZRQ1	SOT-23	DBZ	3	3000	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5013ADEDBZTQ1	SOT-23	DBZ	3	250	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5013ADQDBZRQ1	SOT-23	DBZ	3	3000	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5013ADQDBZTQ1	SOT-23	DBZ	3	250	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5013AGEDBZRQ1	SOT-23	DBZ	3	3000	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5013AGEDBZTQ1	SOT-23	DBZ	3	250	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5013AGQDBZRQ1	SOT-23	DBZ	3	3000	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5013AGQDBZTQ1	SOT-23	DBZ	3	250	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5013BCEDBZRQ1	SOT-23	DBZ	3	3000	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5013BCEDBZTQ1	SOT-23	DBZ	3	250	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5013BCQDBZRQ1	SOT-23	DBZ	3	3000	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5013BCQDBZTQ1	SOT-23	DBZ	3	250	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3
DRV5013FAEDBZRQ1	SOT-23	DBZ	3	3000	180.0	8.4	3.15	2.77	1.22	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV5013ADEDBZJQ1	SOT-23	DBZ	3	10000	346.0	346.0	29.0
DRV5013ADEDBZRQ1	SOT-23	DBZ	3	3000	202.0	201.0	28.0
DRV5013ADEDBZTQ1	SOT-23	DBZ	3	250	202.0	201.0	28.0
DRV5013ADQDBZRQ1	SOT-23	DBZ	3	3000	202.0	201.0	28.0
DRV5013ADQDBZTQ1	SOT-23	DBZ	3	250	202.0	201.0	28.0
DRV5013AGEDBZRQ1	SOT-23	DBZ	3	3000	202.0	201.0	28.0
DRV5013AGEDBZTQ1	SOT-23	DBZ	3	250	202.0	201.0	28.0
DRV5013AGQDBZRQ1	SOT-23	DBZ	3	3000	202.0	201.0	28.0
DRV5013AGQDBZTQ1	SOT-23	DBZ	3	250	202.0	201.0	28.0
DRV5013BCEDBZRQ1	SOT-23	DBZ	3	3000	202.0	201.0	28.0
DRV5013BCEDBZTQ1	SOT-23	DBZ	3	250	202.0	201.0	28.0
DRV5013BCQDBZRQ1	SOT-23	DBZ	3	3000	202.0	201.0	28.0
DRV5013BCQDBZTQ1	SOT-23	DBZ	3	250	202.0	201.0	28.0
DRV5013FAEDBZRQ1	SOT-23	DBZ	3	3000	202.0	201.0	28.0

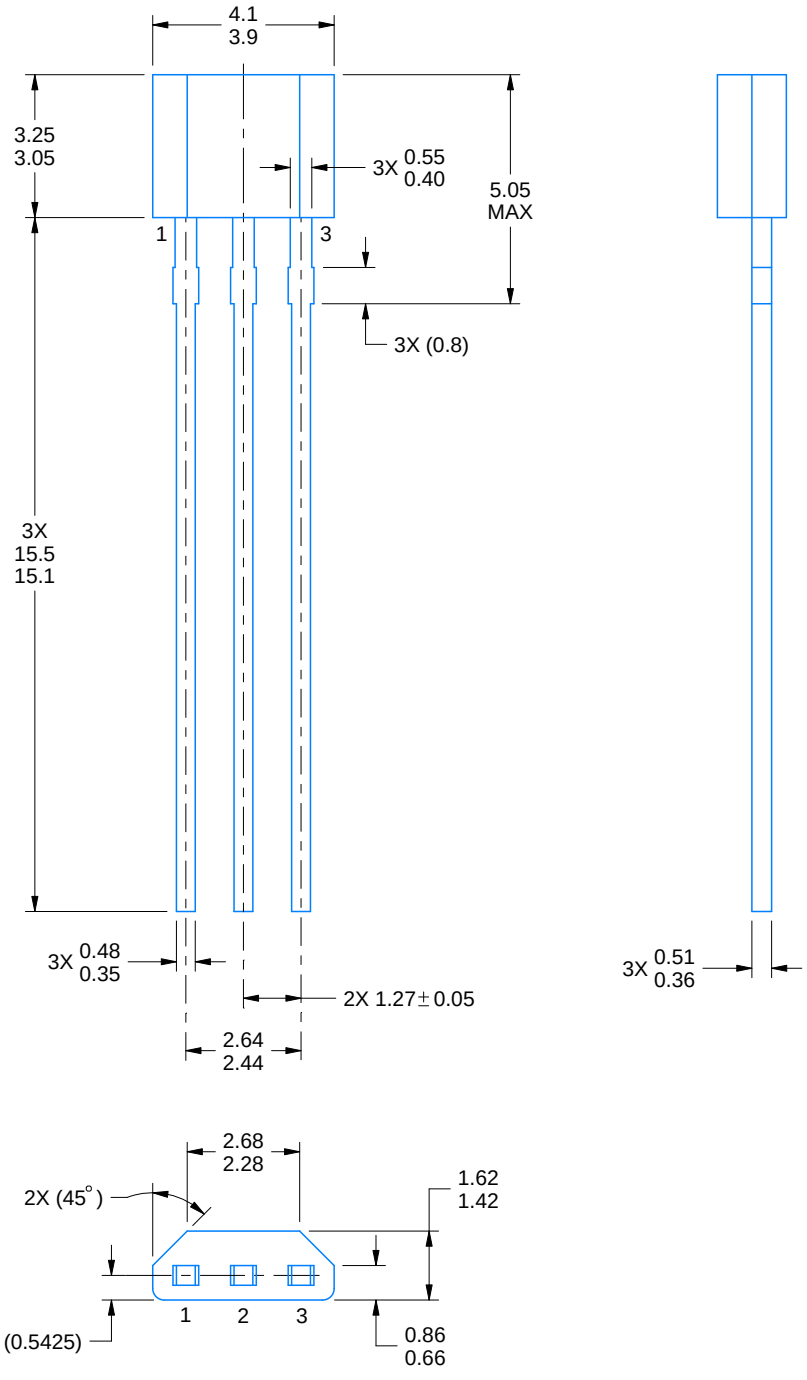


PACKAGE OUTLINE

LPG0003A

TO-92 - 5.05 mm max height

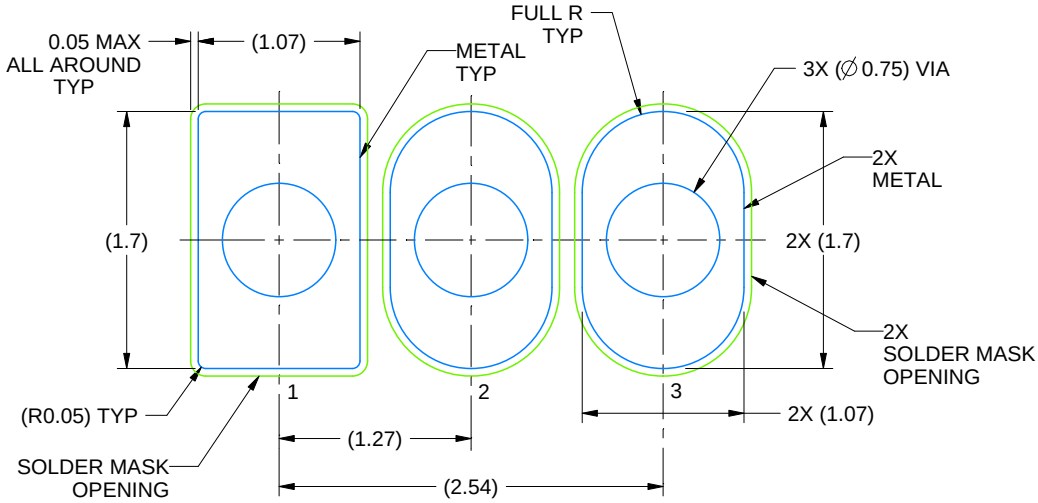
TRANSISTOR OUTLINE



4221343/C 01/2018

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
NON-SOLDER MASK DEFINED
SCALE:20X

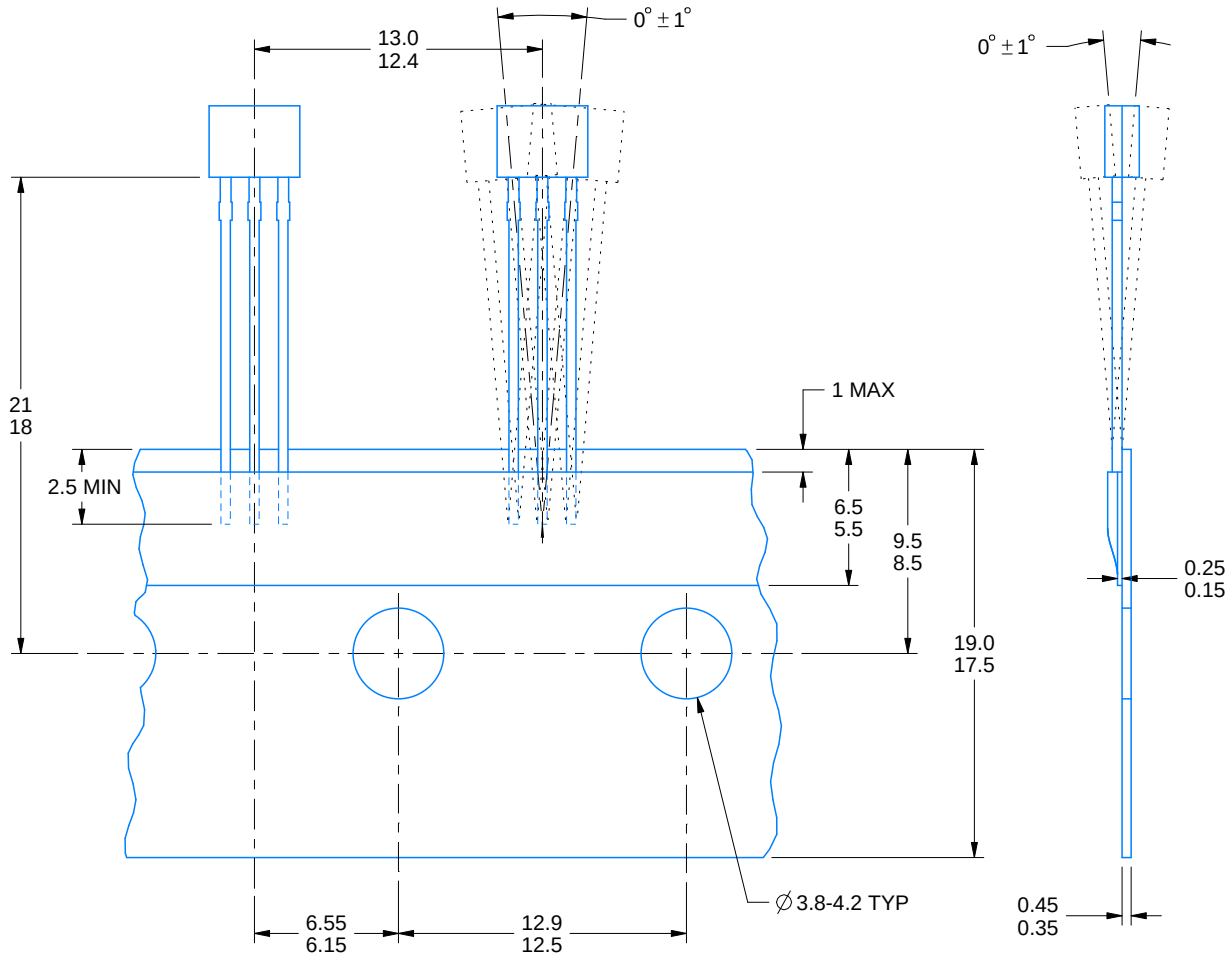
4221343/C 01/2018

TAPE SPECIFICATIONS

LPG0003A

TO-92 - 5.05 mm max height

TRANSISTOR OUTLINE

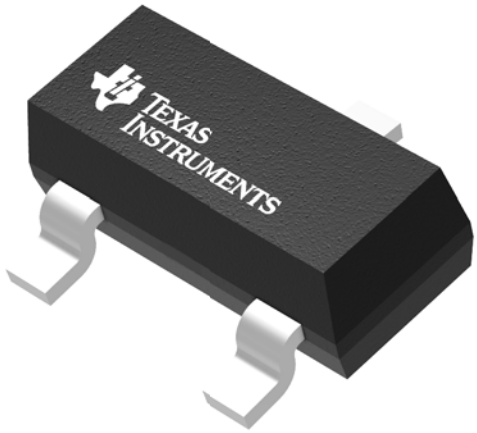


4221343/C 01/2018

GENERIC PACKAGE VIEW

DBZ 3 SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



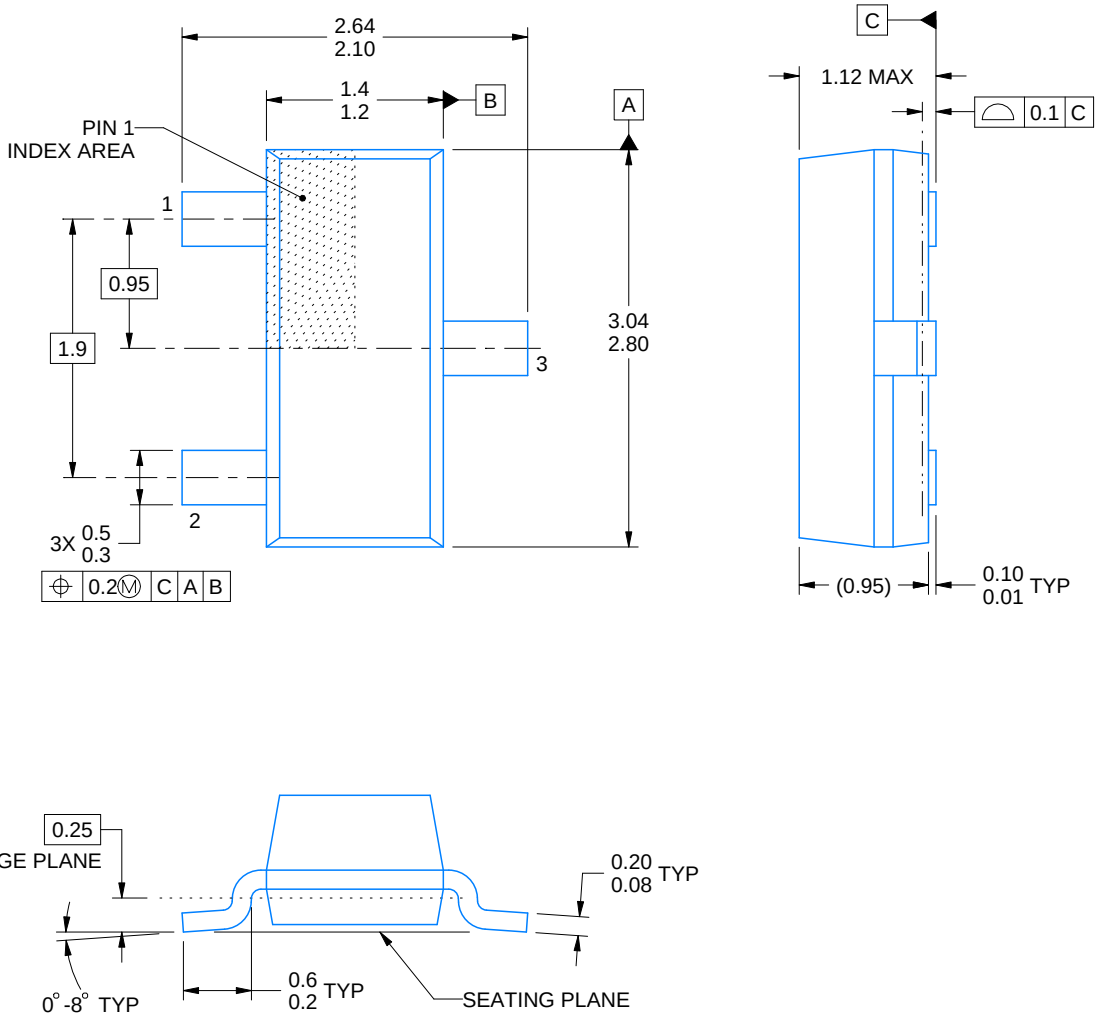
Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

PACKAGE OUTLINE

DBZ0003A

SOT-23 - 1.12 mm max height

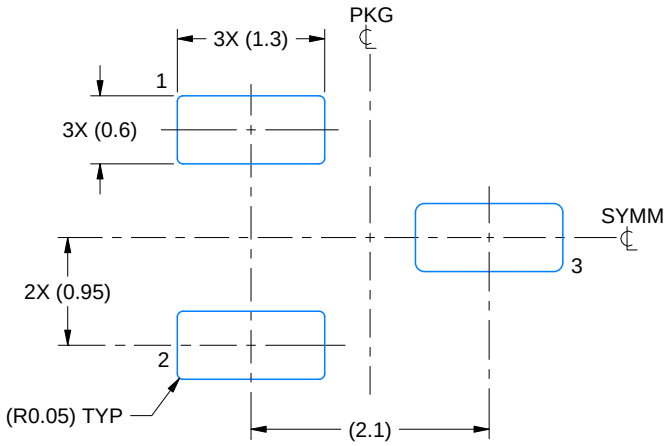
SMALL OUTLINE TRANSISTOR



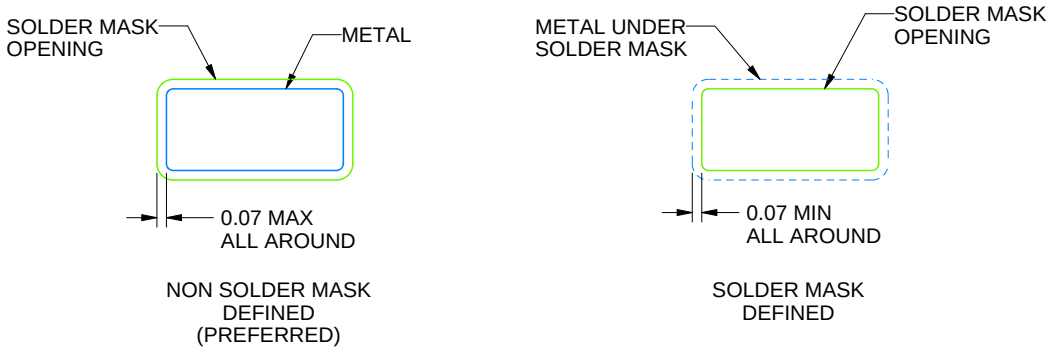
4214838/C 04/2017

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC registration TO-236, except minimum foot length.



LAND PATTERN EXAMPLE
SCALE:15X

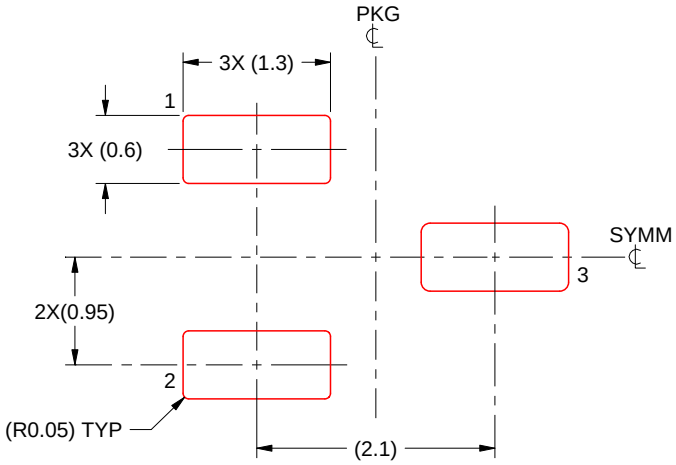


SOLDER MASK DETAILS

4214838/C 04/2017

NOTES: (continued)

4. Publication IPC-7351 may have alternate designs.
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:15X

4214838/C 04/2017

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.

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